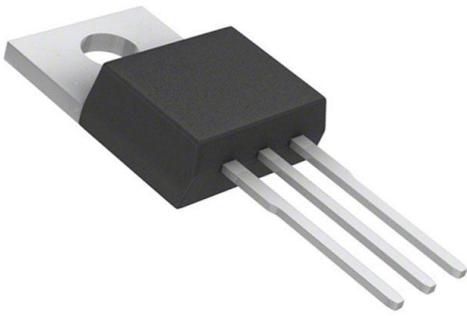


FQP4N50 Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	FQP4N50-DG
Manufacturer	onsemi
Manufacturer Product Number	FQP4N50
Description	MOSFET N-CH 500V 3.4A TO220-3
Detailed Description	N-Channel 500 V 3.4A (Tc) 70W (Tc) Through Hole T O-220-3



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:

FQP4N50

Series:

QFET®

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

500 V

Drive Voltage (Max Rds On, Min Rds On):

10V

Vgs(th) (Max) @ Id:

5V @ 250µA

Vgs (Max):

±30V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

TO-220-3

Base Product Number:

FQP4

Manufacturer:

onsemi

Product Status:

Obsolete

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

3.4A (Tc)

Rds On (Max) @ Id, Vgs:

2.70hm @ 1.7A, 10V

Gate Charge (Qg) (Max) @ Vgs:

13 nC @ 10 V

Input Capacitance (Ciss) (Max) @ Vds:

460 pF @ 25 V

Power Dissipation (Max):

70W (Tc)

Mounting Type:

Through Hole

Package / Case:

TO-220-3

Environmental & Export classification

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

FQP4N50

500V N-Channel MOSFET

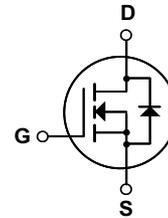
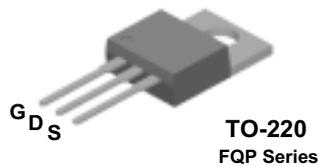
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply, power factor correction, electronic lamp ballast based on half bridge.

Features

- 3.4A, 500V, $R_{DS(on)} = 2.7\Omega @ V_{GS} = 10V$
- Low gate charge (typical 10 nC)
- Low C_{rss} (typical 6.0 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQP4N50	Units
V_{DSS}	Drain-Source Voltage	500	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	3.4	A
		2.15	A
I_{DM}	Drain Current - Pulsed (Note 1)	13.6	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	260	mJ
I_{AR}	Avalanche Current (Note 1)	3.4	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	7.0	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	70	W
		0.56	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	1.79	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.5	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	500	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.38	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 400\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 1.7\text{ A}$	--	2.0	2.7	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 1.7\text{ A}$ (Note 4)	--	2.9	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	350	460	pF
C_{oss}	Output Capacitance		--	55	70	pF
C_{rss}	Reverse Transfer Capacitance		--	6	8	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250\text{ V}, I_D = 3.4\text{ A},$ $R_G = 25\ \Omega$ (Note 4, 5)	--	12	30	ns
t_r	Turn-On Rise Time		--	45	100	ns
$t_{d(off)}$	Turn-Off Delay Time		--	20	50	ns
t_f	Turn-Off Fall Time		--	30	70	ns
Q_g	Total Gate Charge		$V_{DS} = 400\text{ V}, I_D = 3.4\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4, 5)	--	10	13
Q_{gs}	Gate-Source Charge		--	2.5	--	nC
Q_{gd}	Gate-Drain Charge		--	4.7	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	3.4	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	13.6	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 3.4\text{ A}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 3.4\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	210	--	ns
Q_{rr}	Reverse Recovery Charge		--	1.15	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 40\text{mH}, I_{AS} = 3.4\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 3.4\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

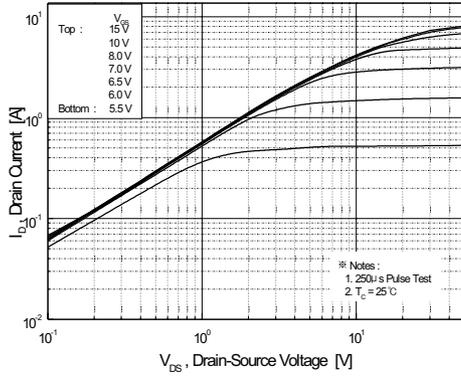


Figure 1. On-Region Characteristics

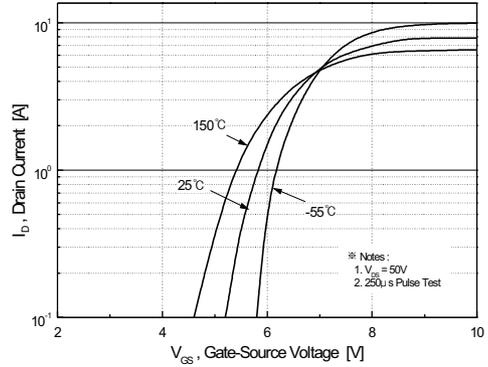


Figure 2. Transfer Characteristics

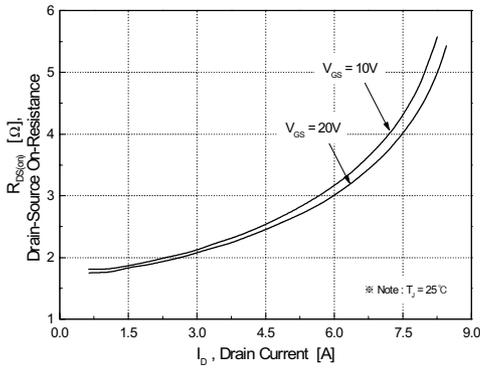


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

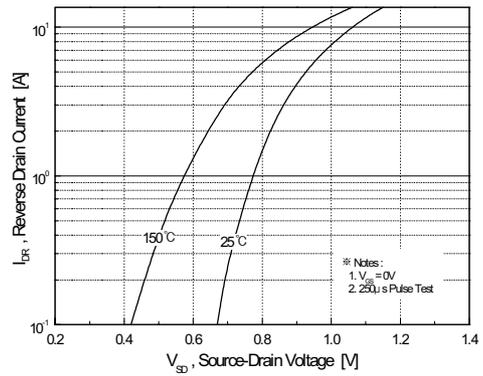


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

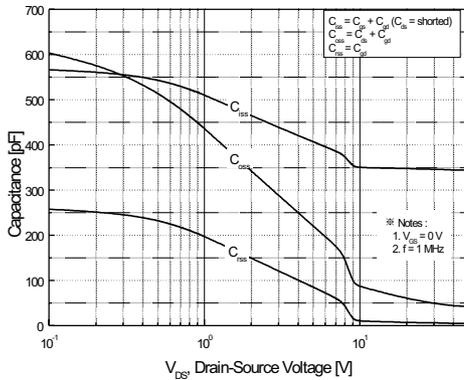


Figure 5. Capacitance Characteristics

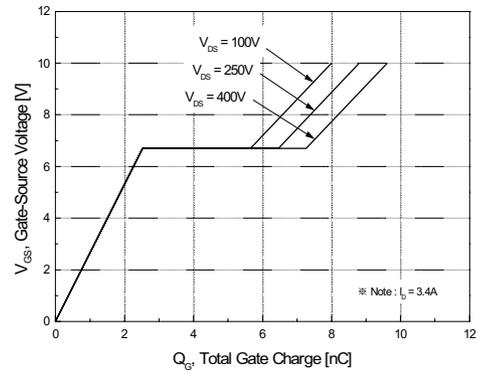


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

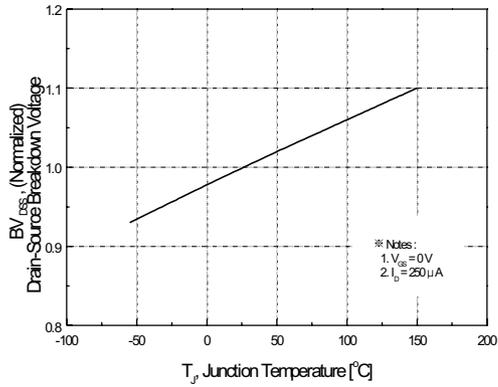


Figure 7. Breakdown Voltage Variation vs. Temperature

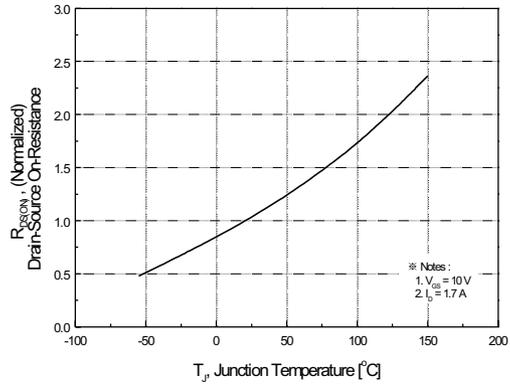


Figure 8. On-Resistance Variation vs. Temperature

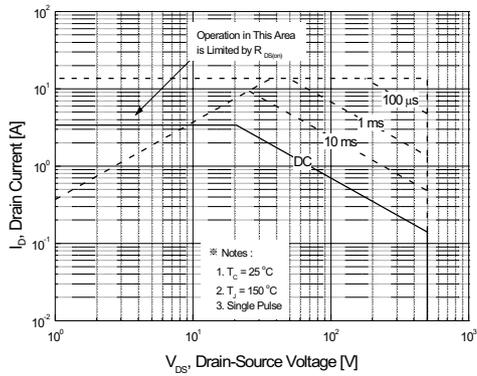


Figure 9. Maximum Safe Operating Area

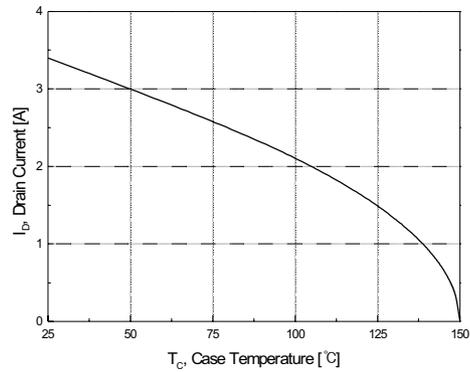


Figure 10. Maximum Drain Current vs. Case Temperature

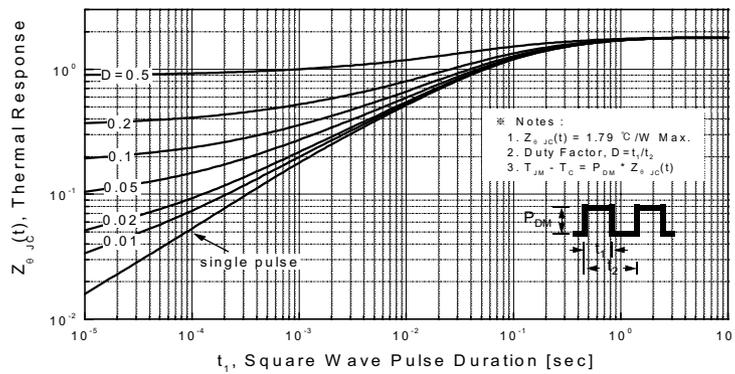
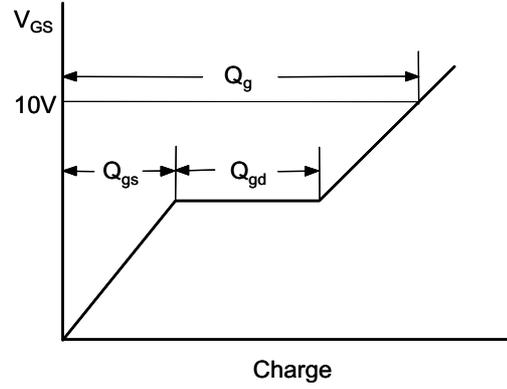
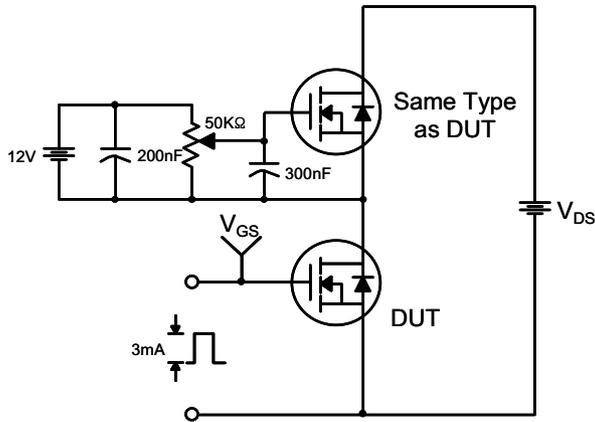
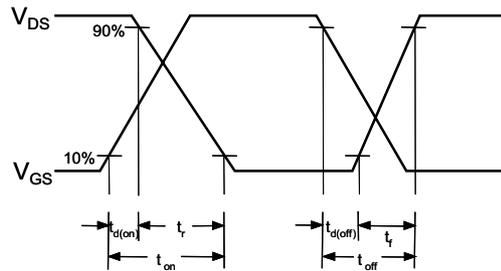
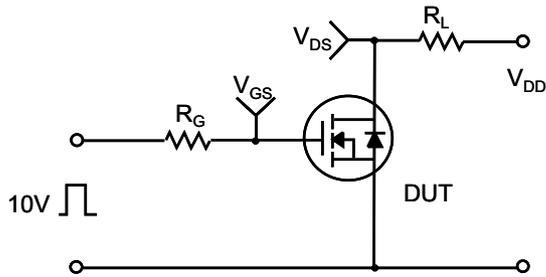


Figure 11. Transient Thermal Response Curve

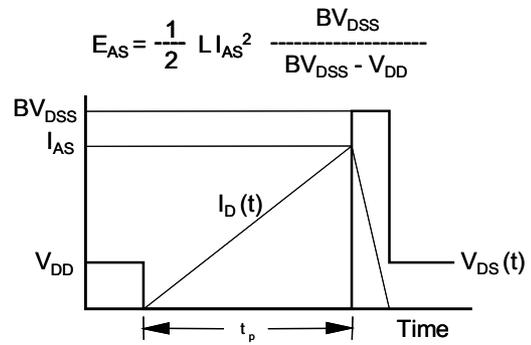
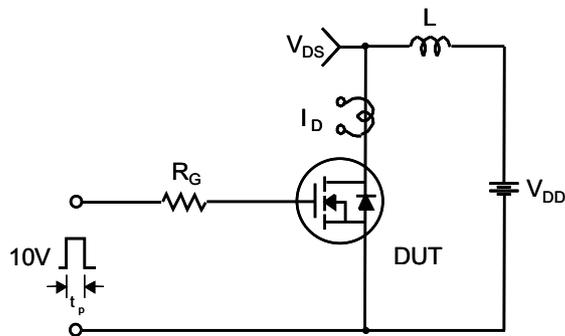
Gate Charge Test Circuit & Waveform



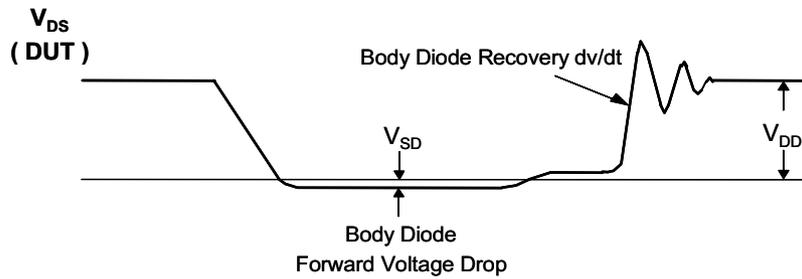
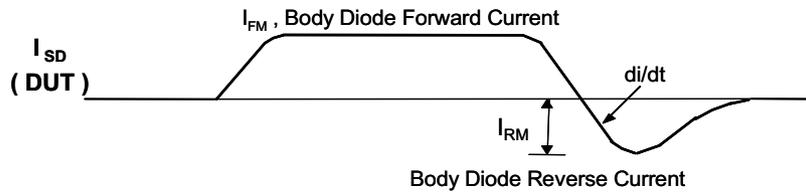
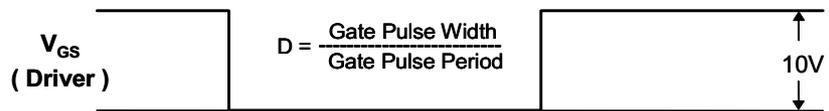
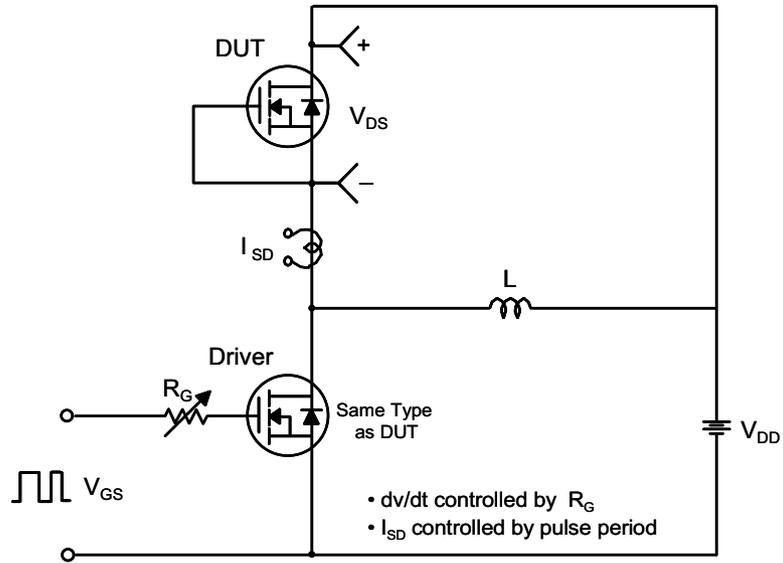
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

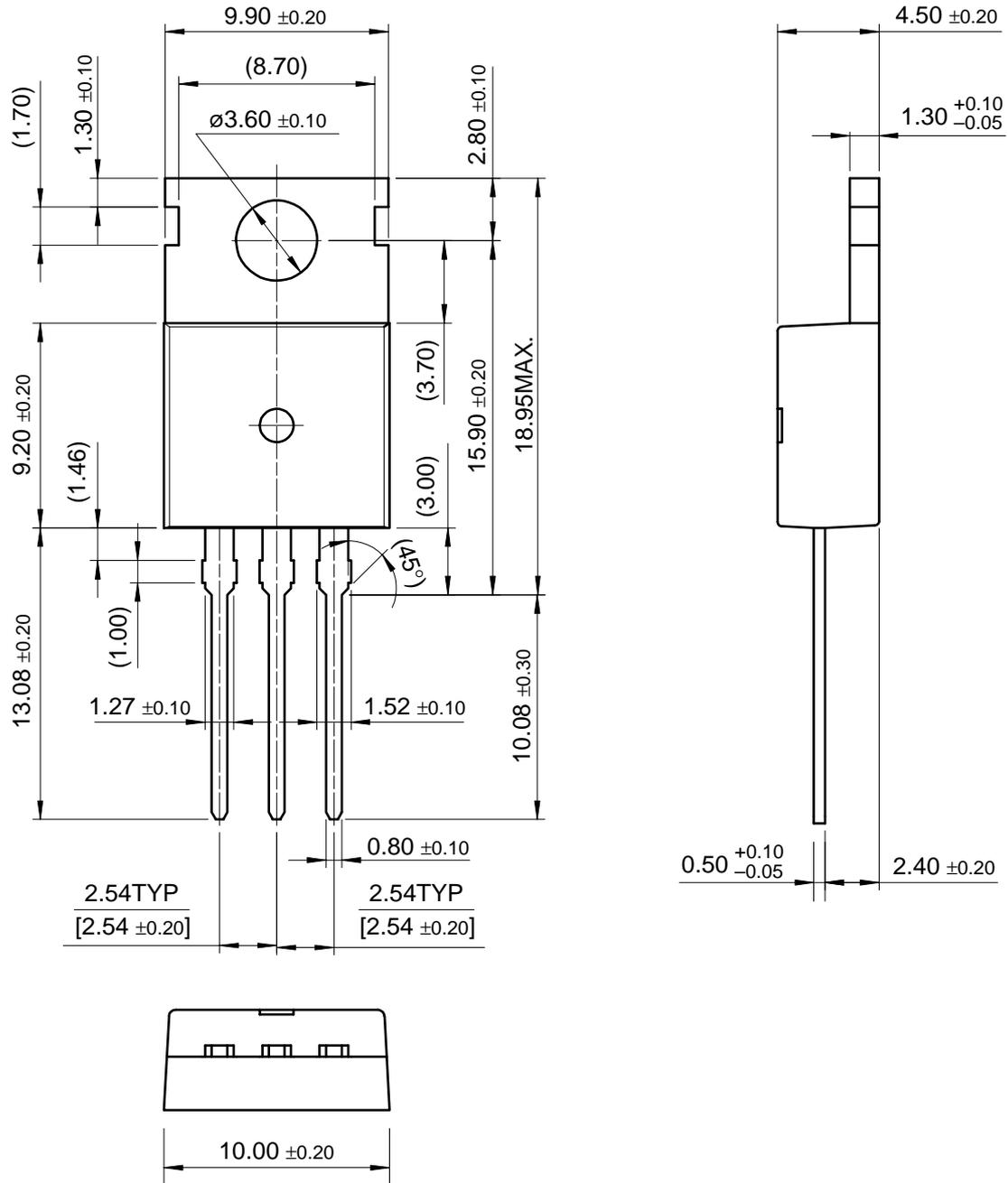


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

TO-220



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